Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
80V	3.3mΩ@10V	110A

合肥矽普半导体
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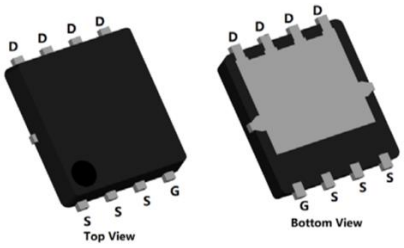
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

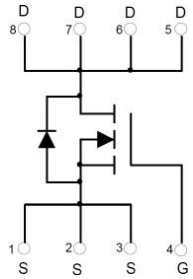
- Power switching application
- DC-DC Converter
- Uninterruptible power supply

Package

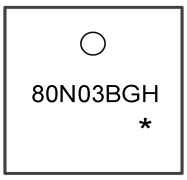


PDFN5X6-8L

Circuit diagram



Marking



80N03BGH :Device Code
*** :Month Code**

Order Information

Device	Package	Unit/Tape
SP80N03BGHNK	PDFN5X6-8L	5000

Absolute maximum ratings (Ta=25℃,unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	80	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (Tc=25°C)	I_D	110	A
Continuous Drain Current (Tc=100°C)	I_D	75	A
Pulse Drain Current Tested	I_{DM}	440	A
Single Pulse Avalanche Energy[1]	E_{AS}	600	mJ
Power Dissipation (Tc=25°C)	P_D	120	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.04	°C/W
Maximum Junction Temperature	T_J	-55 to 150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C

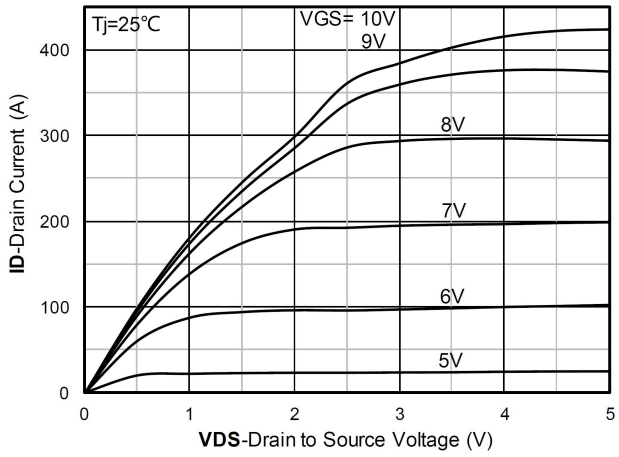
Electrical characteristics (Ta=25℃, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	80	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 64V, V_{GS} = 0V	-	-	1	uA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±0.1	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.0	V
Drain-Source On-state Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A	-	3.3	4.1	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	VGS=0V, VDS=40V,F=1MHz	-	4360	-	pF
Output Capacitance	C_{oss}		-	500	-	
Reverse Transfer Capacitance	C_{rss}		-	26	-	
Total Gate Charge	Q_g	VDS=40V, VGS=10V, ID=20A	-	42	-	nC
Gate-Source Charge	Q_{gs}		-	15	-	
Gate-Drain Charge	Q_{gd}		-	20	-	
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	VDD=40V, ID=20A, VGS=10V, R_G=3Ω	-	17	-	nS
Rise Time	t_r		-	39	-	
Turn-Off Delay Time	$t_{d(off)}$		-	64	-	
Fall Time	t_f		-	42	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I_S		-	-	110	A
Reverse Recovery Time	Trr	I_S=50 A,di/dt=100 A/μs, T_J=25℃	-	45	-	nS
Reverse Recovery Charge	Qrr		-	56	-	nC

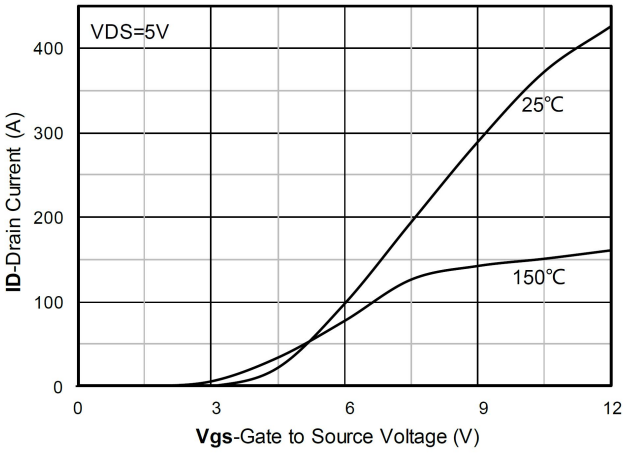
Note :

1. The test condition is VDD=40V,VGS=10V,L=0.5mH,RG=25Ω

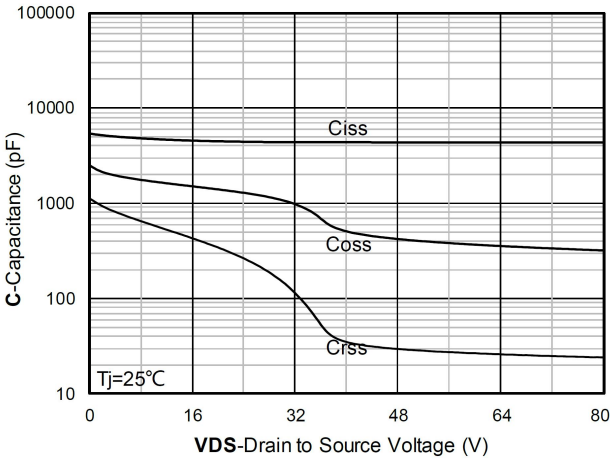
Typical Characteristics



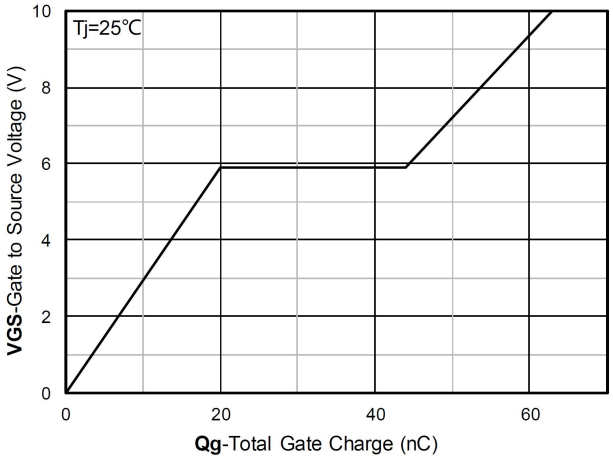
Output Characteristics



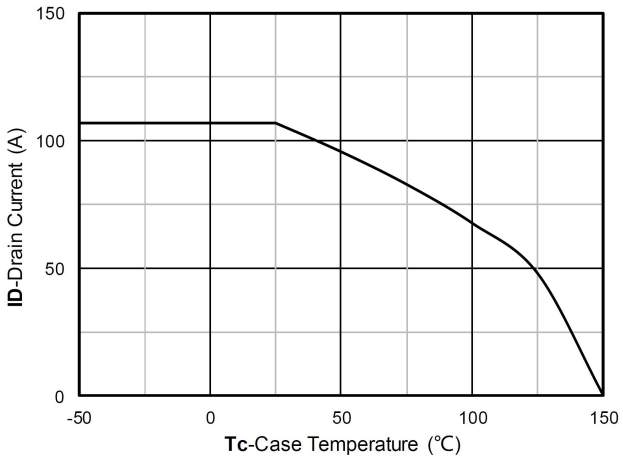
Transfer Characteristics



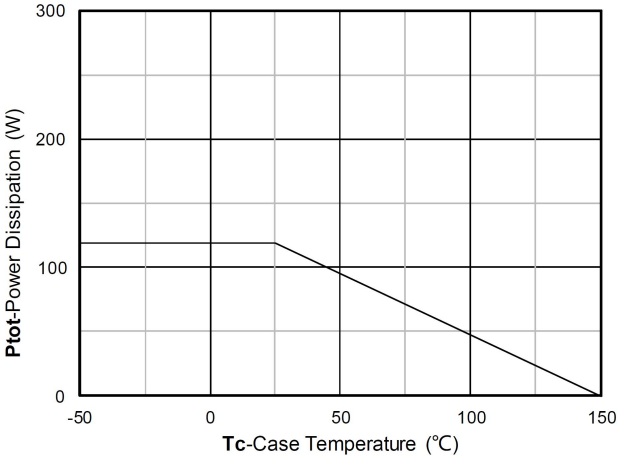
Capacitance Characteristics



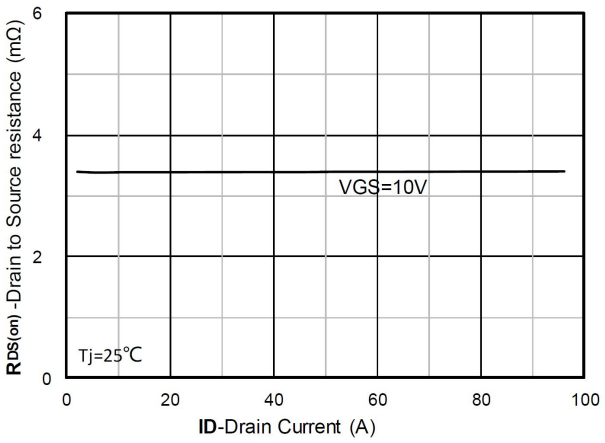
Gate Charge



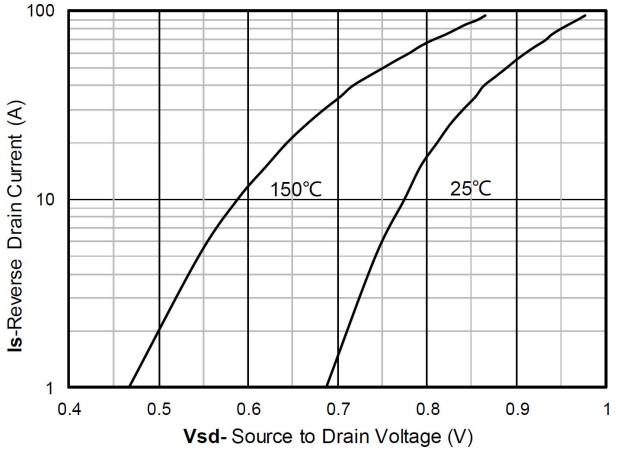
Current dissipation



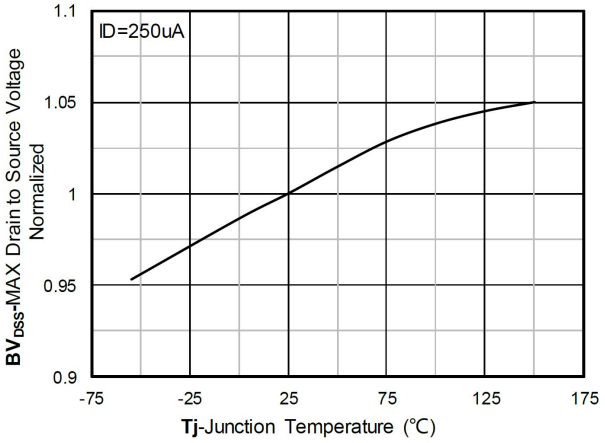
Power dissipation



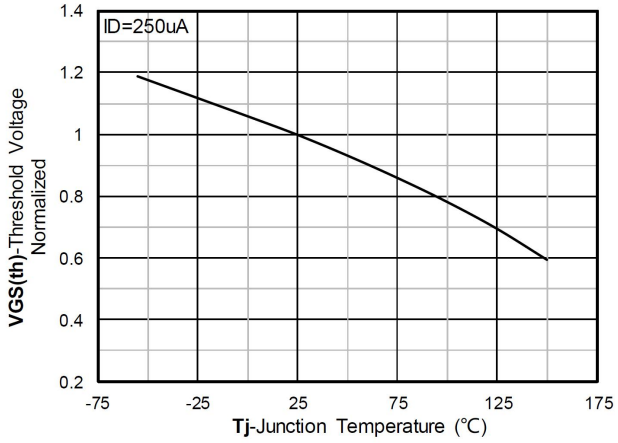
RDS(on) VS Drain Current



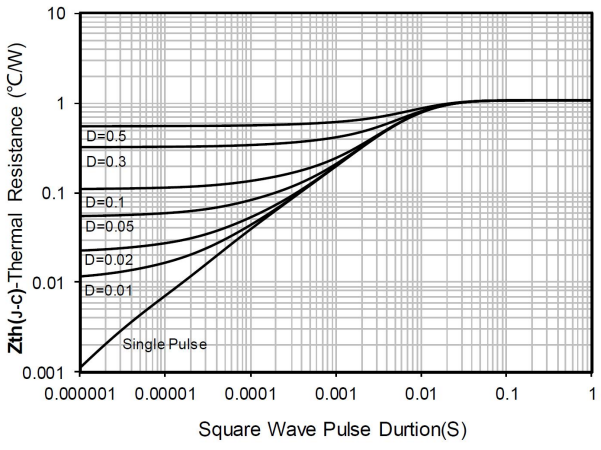
Forward characteristics of reverse diode



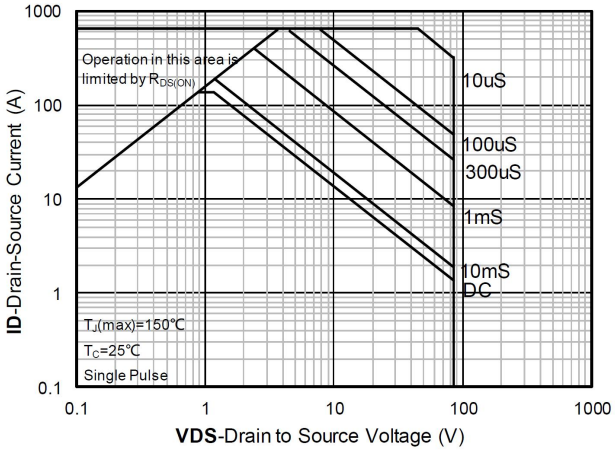
Normalized breakdown voltage



Normalized Threshold voltage

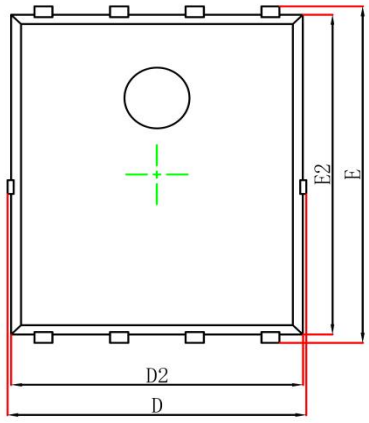


Maximum Transient Thermal Impedance

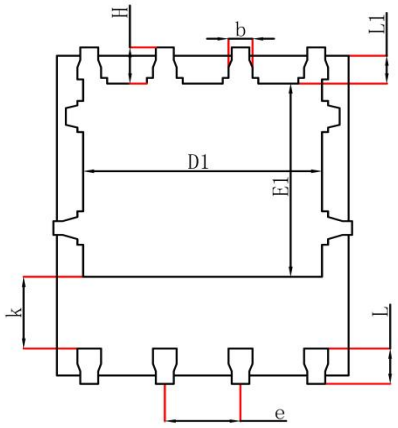


Safe Operation Area

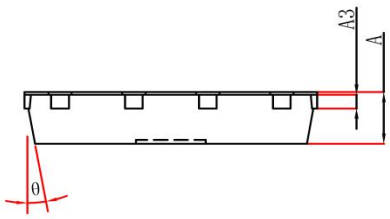
PDFN5X6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°